

1. Material Substrate GaAs (N Type)
 Epitaxial Layer AlGaInP (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
 P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F		2.1	2.4	V	IF=20mA
Reverse Current	I_R			100	uA	VR=5V
Brightness	I_v	A	80	100	mcd	IF=20mA
		B	100	120		
		C	120	140		
		D	140	160		
Wavelength	λ_d		620		nm	IF=20mA
	$\Delta\lambda$		20		nm	IF=20mA

※ Note : Luminous Intensity is measured on bare chips.

4. Mechanical Data (a) Emission Area ----- 8mil x 8mil
 (b) Bottom Area ----- 9mil x 9mil
 (c) Bonding Pad ----- 100um
 (d) Chip Thickness ----- 7mil

